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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

260 papers	4,649 citations	34 h-index	56 g-index
296 ext. papers	5,205 ext. citations	2.4 avg, IF	5.46 L-index

#	Paper	IF	Citations
260	Interfacial characteristics of N ₂ O and NO nitrided SiO ₂ grown on SiC by rapid thermal processing. <i>Applied Physics Letters</i> , 1997 , 70, 2028-2030	3.4	251
259	Effects of nitridation in gate oxides grown on 4H-SiC. <i>Journal of Applied Physics</i> , 2001 , 90, 5058-5063	2.5	223
258	Mechanisms responsible for improvement of 4H-BiC/SiO ₂ interface properties by nitridation. <i>Applied Physics Letters</i> , 2003 , 82, 568-570	3.4	170
257	The Piezoresistive Effect of SiC for MEMS Sensors at High Temperatures: A Review. <i>Journal of Microelectromechanical Systems</i> , 2015 , 24, 1663-1677	2.5	150
256	Band alignment and defect states at SiC/oxide interfaces. <i>Journal of Physics Condensed Matter</i> , 2004 , 16, S1839-S1856	1.8	130
255	Physical properties of N ₂ O and NO-nitrided gate oxides grown on 4H SiC. <i>Applied Physics Letters</i> , 2001 , 79, 323-325	3.4	118
254	Investigation of nitric oxide and Ar annealed SiO ₂ /SiC interfaces by x-ray photoelectron spectroscopy. <i>Journal of Applied Physics</i> , 1999 , 86, 4316-4321	2.5	91
253	Growth of 3C-BiC on 150-mm Si(100) substrates by alternating supply epitaxy at 1000 °C. <i>Thin Solid Films</i> , 2011 , 519, 6443-6446	2.2	78
252	Electrical and physical characterization of gate oxides on 4H-SiC grown in diluted N ₂ O. <i>Journal of Applied Physics</i> , 2003 , 93, 5682-5686	2.5	69
251	Nitridation of silicon-dioxide films grown on 6H silicon carbide. <i>IEEE Electron Device Letters</i> , 1997 , 18, 175-177	4.4	68
250	High quality ultrathin dielectric films grown on silicon in a nitric oxide ambient. <i>Applied Physics Letters</i> , 1994 , 64, 3584-3586	3.4	68
249	Advances in SiC power MOSFET technology. <i>Microelectronics Reliability</i> , 2003 , 43, 225-233	1.2	63
248	Mechanism of Threshold Voltage Shift in $\text{p}^+\text{-GaN}$ Gate AlGa _{0.3} N/GaN Transistors. <i>IEEE Electron Device Letters</i> , 2018 , 39, 1145-1148	4.4	61
247	Analysis of CMOS transistor instabilities. <i>Solid-State Electronics</i> , 1987 , 30, 991-1003	1.7	61
246	Fundamental piezoresistive coefficients of p-type single crystalline 3C-SiC. <i>Applied Physics Letters</i> , 2014 , 104, 111905	3.4	59
245	Enhanced channel mobility of 4H-BiC metal-oxide-semiconductor transistors fabricated with standard polycrystalline silicon technology and gate-oxide nitridation. <i>Applied Physics Letters</i> , 2002 , 80, 4253-4255	3.4	54
244	Demonstration of p-type 3C-BiC grown on 150 mm Si(1 0 0) substrates by atomic-layer epitaxy at 1000 °C. <i>Journal of Crystal Growth</i> , 2011 , 329, 67-70	1.6	53

243	Permutation-based DCSK and multiple-access DCSK systems. <i>IEEE Transactions on Circuits and Systems Part 1: Regular Papers</i> , 2003 , 50, 733-742		53
242	Surface-Passivation Effects on the Performance of 4H-SiC BJTs. <i>IEEE Transactions on Electron Devices</i> , 2011 , 58, 259-265	2.9	50
241	Ultrathin Fe ₂ O ₃ nanoflakes using smart chemical stripping for high performance lithium storage. <i>Journal of Materials Chemistry A</i> , 2017 , 5, 18737-18743	13	48
240	Piezoresistive effect in p-type 3C-SiC at high temperatures characterized using Joule heating. <i>Scientific Reports</i> , 2016 , 6, 28499	4.9	47
239	Thickness dependence of the piezoresistive effect in p-type single crystalline 3C-SiC nanothin films. <i>Journal of Materials Chemistry C</i> , 2014 , 2, 7176-7179	7.1	47
238	Power-switching applications beyond silicon: Status and future prospects of SiC and GaN devices. <i>MRS Bulletin</i> , 2015 , 40, 399-405	3.2	46
237	Transient-Current Method for Measurement of Active Near-Interface Oxide Traps in 4H-SiC MOS Capacitors and MOSFETs. <i>IEEE Transactions on Electron Devices</i> , 2015 , 62, 2670-2674	2.9	45
236	A catalytic alloy approach for graphene on epitaxial SiC on silicon wafers. <i>Journal of Materials Research</i> , 2015 , 30, 609-616	2.5	43
235	A study of cross-linked PEO gel polymer electrolytes using bisphenol A ethoxylate diacrylate: ionic conductivity and mechanical properties. <i>Journal of Power Sources</i> , 2003 , 119-121, 432-437	8.9	43
234	Piezoresistive Effect of p-Type Single Crystalline 3C-SiC Thin Film. <i>IEEE Electron Device Letters</i> , 2014 , 35, 399-401	4.4	42
233	Improved reliability of NO-nitrided SiO ₂ grown on p-type 4H-SiC. <i>IEEE Electron Device Letters</i> , 1998 , 19, 279-281	4.4	41
232	Active defects in MOS devices on 4H-SiC: A critical review. <i>Microelectronics Reliability</i> , 2016 , 60, 1-9	1.2	40
231	Slow-trap profiling of NO and N ₂ O nitrided oxides grown on Si and SiC substrates. <i>Microelectronics Reliability</i> , 1999 , 39, 441-449	1.2	37
230	. <i>IEEE Electron Device Letters</i> , 1995 , 16, 345-347	4.4	37
229	Controlling a DC-DC converter by using the power MOSFET as a voltage controlled resistor. <i>IEEE Transactions on Circuits and Systems Part 1: Regular Papers</i> , 2000 , 47, 357-362		36
228	Analysis of gamma-radiation induced instability mechanisms in CMOS transistors. <i>Solid-State Electronics</i> , 1989 , 32, 349-353	1.7	36
227	Synthesis of Zn(II) 5,10,15,20-tetrakis(4-isopropylphenyl) porphyrin and its use as a thin film sensor. <i>Applied Physics A: Materials Science and Processing</i> , 2010 , 98, 103-109	2.6	35
226	Energy position of the active near-interface traps in metaloxide semiconductor field-effect transistors on 4H-SiC. <i>Applied Physics Letters</i> , 2013 , 103, 113506	3.4	34

225	. <i>IEEE Electron Device Letters</i> , 1994 , 15, 516-518	4.4	34
224	Experimental Investigation of Piezoresistive Effect in p-Type 4H-SiC. <i>IEEE Electron Device Letters</i> , 2017 , 38, 955-958	4.4	33
223	Analysis of current conduction mechanisms in atomic-layer-deposited Al ₂ O ₃ gate on 4H silicon carbide. <i>Applied Physics Letters</i> , 2007 , 90, 162113	3.4	33
222	Model for dielectric growth on silicon in a nitrous oxide environment. <i>Applied Physics Letters</i> , 1993 , 62, 1539-1540	3.4	32
221	Analysis of subthreshold carrier transport for ultimate DGMOSFET. <i>IEEE Transactions on Electron Devices</i> , 2006 , 53, 685-691	2.9	31
220	Analysis of gamma-irradiation induced degradation mechanisms in power VDMOSFETs. <i>Microelectronics Reliability</i> , 1995 , 35, 587-602	1.2	31
219	Excellent Rectifying Properties of the n-3C-SiC/p-Si Heterojunction Subjected to High Temperature Annealing for Electronics, MEMS, and LED Applications. <i>Scientific Reports</i> , 2017 , 7, 17734	4.9	30
218	Effects of nitrogen incorporation on the interfacial layer between thermally grown dielectric films and SiC. <i>Applied Physics Letters</i> , 2009 , 94, 251909	3.4	30
217	Traps at the Interface of 3C-SiC/SiO ₂ -MOS-Structures. <i>Materials Science Forum</i> , 2003 , 433-436, 551-554	0.4	30
216	Mechanisms of positive gate bias stress induced instabilities in power VDMOSFETs. <i>Microelectronics Reliability</i> , 2001 , 41, 1373-1378	1.2	30
215	Modeling the growth of thin silicon oxide films on silicon. <i>Journal of Applied Physics</i> , 1996 , 80, 2467-2470	2.5	30
214	Instabilities in MOS transistors. <i>Microelectronics Reliability</i> , 1989 , 29, 371-380	1.2	30
213	SiC/SiO ₂ Interface States: Properties and Models. <i>Materials Science Forum</i> , 2005 , 483-485, 563-568	0.4	29
212	Effects of thermal nitrided gate-oxide thickness on 4H silicon-carbide-based metal-oxide-semiconductor characteristics. <i>Applied Physics Letters</i> , 2007 , 90, 012120	3.4	28
211	SIMS analysis of nitrided oxides grown on 4H-SiC. <i>Journal of Electronic Materials</i> , 1999 , 28, 109-111	1.9	28
210	The effect of strain on the electrical conductance of p-type nanocrystalline silicon carbide thin films. <i>Journal of Materials Chemistry C</i> , 2015 , 3, 1172-1176	7.1	27
209	Inter-image outliers and their application to image classification. <i>Pattern Recognition</i> , 2010 , 43, 4101-4112	1.7	27
208	Effect of NO annealing conditions on electrical characteristics of n-type 4H-SiC MOS capacitors. <i>Journal of Electronic Materials</i> , 2000 , 29, 1027-1032	1.9	26

207	The determination of zero temperature coefficient point in CMOS transistors. <i>Microelectronics Reliability</i> , 1992 , 32, 769-773	1.2	25
206	Orientation dependence of the pseudo-Hall effect in p-type 3C-SiC four-terminal devices under mechanical stress. <i>RSC Advances</i> , 2015 , 5, 56377-56381	3.7	24
205	Metal-oxide-semiconductor characteristics of thermally grown nitrided SiO ₂ thin film on 4H-SiC in various N ₂ O ambient. <i>Thin Solid Films</i> , 2010 , 518, 3255-3259	2.2	24
204	The effect of device geometry and crystal orientation on the stress-dependent offset voltage of 3C-SiC(100) four terminal devices. <i>Journal of Materials Chemistry C</i> , 2015 , 3, 8804-8809	7.1	23
203	The Dependence of Offset Voltage in p-Type 3C-SiC van der Pauw Device on Applied Strain. <i>IEEE Electron Device Letters</i> , 2015 , 36, 708-710	4.4	23
202	Formation of Zr-oxynitride thin films on 4H-SiC substrate. <i>Thin Solid Films</i> , 2012 , 520, 6822-6829	2.2	22
201	Enhanced electrostatic force generation capability of angled comb finger design used in electrostatic comb-drive actuators. <i>Electronics Letters</i> , 1998 , 34, 1787	1.1	22
200	. <i>IEEE Transactions on Electron Devices</i> , 1994 , 41, 2210-2215	2.9	22
199	Influence of post-deposition annealing in oxygen ambient on metal-organic decomposed CeO ₂ film spin coated on 4H-SiC. <i>Journal of Materials Science: Materials in Electronics</i> , 2012 , 23, 257-266	2.1	20
198	Physical characterization of post-deposition annealed metal-organic decomposed cerium oxide film spin-coated on 4H-silicon carbide. <i>Journal of Alloys and Compounds</i> , 2010 , 497, 195-200	5.7	20
197	Nearest Neighbor Classifier Based on Nearest Feature Decisions. <i>Computer Journal</i> , 2012 , 55, 1072-1087	1.3	20
196	Analysis of charge conduction mechanisms in nitrided SiO ₂ Film on 4H SiC. <i>Physics Letters, Section A: General, Atomic and Solid State Physics</i> , 2008 , 372, 529-532	2.3	20
195	Effects of electrical stressing in power VDMOSFETs. <i>Microelectronics Reliability</i> , 2005 , 45, 115-122	1.2	20
194	Analysis of Fowler-Nordheim injection in NO nitrided gate oxide grown on n-type 4H-SiC. <i>Microelectronics Reliability</i> , 2000 , 40, 283-286	1.2	20
193	MOS Characteristics of Metallorganic-Decomposed CeO ₂ Spin-Coated on GaN. <i>Electrochemical and Solid-State Letters</i> , 2010 , 13, H116		19
192	Transition between amorphous and crystalline phases of SiC deposited on Si substrate using H ₃ SiCH ₃ . <i>Journal of Crystal Growth</i> , 2009 , 311, 4442-4446	1.6	19
191	Investigation of sol-gel derived HfO ₂ on 4H-SiC. <i>Applied Surface Science</i> , 2008 , 254, 1981-1985	6.7	19
190	Channel-carrier mobility parameters for 4H SiC MOSFETs. <i>Microelectronics Reliability</i> , 2003 , 43, 405-411	1.2	19

189	Description and Verification of the Fundamental Current Mechanisms in Silicon Carbide Schottky Barrier Diodes. <i>Scientific Reports</i> , 2019 , 9, 3754	4.9	18
188	Misorientation dependent epilayer tilting and stress distribution in heteroepitaxially grown silicon carbide on silicon (111) substrate. <i>Thin Solid Films</i> , 2014 , 564, 39-44	2.2	18
187	Charge Trapping Properties of 3C- and 4H-SiC MOS Capacitors With Nitrided Gate Oxides. <i>IEEE Transactions on Nuclear Science</i> , 2009 , 56, 3185-3191	1.7	18
186	Genetic variation in heat shock protein 70 is associated with septic shock: narrowing the association to a specific haplotype. <i>International Journal of Immunogenetics</i> , 2008 , 35, 465-73	2.3	18
185	Effects of high electric field and elevated-temperature bias stressing on radiation response in power VDMOSFETs. <i>Microelectronics Reliability</i> , 2002 , 42, 669-677	1.2	18
184	MOS capacitor on 4H-SiC as a nonvolatile memory element. <i>IEEE Electron Device Letters</i> , 2002 , 23, 404-406	0.4	18
183	Electrical stressing effects in commercial power VDMOSFETs. <i>IET Circuits, Devices and Systems</i> , 2006 , 153, 281		17
182	A P-Channel MOSFET on 4H-SiC. <i>Materials Science Forum</i> , 2004 , 457-460, 1401-1404	0.4	17
181	Alleles of the proximal promoter of BAT1, a putative anti-inflammatory gene adjacent to the TNF cluster, reduce transcription on a disease-associated MHC haplotype. <i>Genes To Cells</i> , 2003 , 8, 403-12	2.3	17
180	Effects of Initial Nitridation on the Characteristics of SiC-SiO ₂ Interfaces. <i>Materials Science Forum</i> , 2003 , 433-436, 583-586	0.4	17
179	Anisotropy of hole structures in polymers probed by two-dimensional angular correlation of annihilation radiation. <i>Physical Review B</i> , 1996 , 54, 1785-1790	3.3	17
178	Pseudo-Hall effect in single crystal 3C-SiC(111) four-terminal devices. <i>Journal of Materials Chemistry C</i> , 2015 , 3, 12394-12398	7.1	16
177	Sequential thermal treatments of SiC in NO and O ₂ : Atomic transport and electrical characteristics. <i>Applied Physics Letters</i> , 2007 , 91, 041906	3.4	16
176	Extension of the Deal-Grove oxidation model to include the effects of nitrogen. <i>IEEE Transactions on Electron Devices</i> , 1996 , 43, 267-272	2.9	16
175	Highly sensitive p-type 4H-SiC van der Pauw sensor.. <i>RSC Advances</i> , 2018 , 8, 3009-3013	3.7	15
174	Ag/PEPC/NiPc/ZnO/Ag thin film capacitive and resistive humidity sensors. <i>Journal of Semiconductors</i> , 2010 , 31, 054002	2.3	15
173	Stimulation of silicon carbide nanotubes formation using different ratios of carbon nanotubes to silicon dioxide nanopowders. <i>Journal of Alloys and Compounds</i> , 2009 , 475, 565-568	5.7	15
172	Formation and characterization of SiO _x nanowires and Si/SiO _x core-shell nanowires via carbon-assisted growth. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2010 , 42, 1338-1342	3	15

171	The microsatellite, macrophage migration inhibitory factor -794, may influence gene expression in human mononuclear cells stimulated with E. coli or S. pneumoniae. <i>International Journal of Immunogenetics</i> , 2008 , 35, 309-16	2.3	15
170	Effects of rapid thermal annealing on nitrided gate oxide grown on 4H-SiC. <i>Microelectronic Engineering</i> , 2006 , 83, 65-71	2.5	15
169	Current conduction mechanisms in post-nitridation rapid-thermal-annealed gate oxides on 4H silicon carbide. <i>Applied Physics Letters</i> , 2005 , 87, 212102	3.4	15
168	Novel SiC accumulation-mode power MOSFET. <i>IEEE Transactions on Electron Devices</i> , 2001 , 48, 1711-1717	2.9	15
167	Technique for monitoring slow interface trap characteristics in MOS capacitors. <i>Electronics Letters</i> , 1995 , 31, 1880-1881	1.1	15
166	Direct Measurement of Active Near-Interface Traps in the Strong-Accumulation Region of 4H-SiC MOS Capacitors. <i>IEEE Journal of the Electron Devices Society</i> , 2018 , 6, 468-474	2.3	14
165	Face Recognition Using Local Binary Decisions. <i>IEEE Signal Processing Letters</i> , 2008 , 15, 821-824	3.2	14
164	Effects of annealing temperature on ultra-low dielectric constant SiO ₂ thin films derived from sol-gel spin-on-coating. <i>Physica B: Condensed Matter</i> , 2008 , 403, 611-615	2.8	14
163	Investigation of ultralow leakage in MOS capacitors on 4H SiC. <i>IEEE Transactions on Electron Devices</i> , 2004 , 51, 1361-1365	2.9	14
162	Effect of Hole-Injection on Leakage Degradation in a p-GaN Gate AlGaIn/GaN Power Transistor. <i>IEEE Electron Device Letters</i> , 2018 , 39, 1203-1206	4.4	13
161	Electrical Characteristics of Near-Interface Traps in 3C-SiC Metal-Oxide-Semiconductor Capacitors. <i>IEEE Electron Device Letters</i> , 2008 , 29, 1021-1023	4.4	13
160	Charge retention in metal-oxide-semiconductor capacitors on SiC used as nonvolatile-memory elements. <i>Applied Physics Letters</i> , 2002 , 80, 3421-3423	3.4	13
159	Gate-Voltage Independence of Electron Mobility in Power AlGaIn/GaN HEMTs. <i>IEEE Transactions on Electron Devices</i> , 2016 , 63, 1013-1019	2.9	12
158	Vertically Conductive Single-Crystal SiC-Based Bragg Reflector Grown on Si Wafer. <i>Scientific Reports</i> , 2015 , 5, 17026	4.9	12
157	The accuracy of surrogate decisions in intensive care scenarios. <i>Anaesthesia and Intensive Care</i> , 2007 , 35, 46-51	1.1	12
156	Can MHC class II genes mediate resistance to type 1 diabetes?. <i>Immunology and Cell Biology</i> , 2001 , 79, 602-6	5	12
155	Passivation of the Oxide/4H-SiC Interface. <i>Materials Science Forum</i> , 2002 , 389-393, 973-976	0.4	12
154	The Power Law of Phonon-Limited Electron Mobility in the 2-D Electron Gas of AlGaIn/GaN Heterostructure. <i>IEEE Transactions on Electron Devices</i> , 2016 , 63, 2214-2218	2.9	12

- 153 Memristor pattern recogniser: isolated speech word recognition. *Electronics Letters*, **2015**, 51, 1370-1372. 11
- 152 Effect of Postoxidation Annealing on High Temperature Grown SiO₂/4H-SiC Interfaces. *Journal of the Electrochemical Society*, **2010**, 157, H196 3.9 11
- 151 Modeling Radiation-Induced Mobility Degradation in MOSFETs. *Physica Status Solidi A*, **1998**, 169, 63-66 11
- 150 Permutation-Based M-ary Chaotic-Sequence Spread-Spectrum Communication Systems. *Circuits, Systems, and Signal Processing*, **2003**, 22, 567-577 2.2 11
- 149 Central MHC genes affect IgA levels in the human: reciprocal effects in IgA deficiency and IgA nephropathy. *Human Immunology*, **2002**, 63, 424-33 2.3 11
- 148 Analysis of a multiresonant forward converter based on nonideal coupling of the transformer. *IEEE Transactions on Power Electronics*, **2000**, 15, 111-120 7.2 11
- 147 Novel Electrical Characterization of Thin 3C-SiC Films on Si Substrates. *Science of Advanced Materials*, **2014**, 6, 1542-1547 2.3 11
- 146 Optically Active Defects at the SiC/SiO₂ Interface. *Physical Review Applied*, **2019**, 12, 4.3 10
- 145 SiC power MOSFETs: The current status and the potential for future development **2017**, 10
- 144 Enhanced photoelectrocatalytic performance of etched 3C-SiC thin film for water splitting under visible light. *RSC Advances*, **2014**, 4, 54441-54446 3.7 10
- 143 SiC-based Piezoelectric Energy Harvester for Extreme Environment. *Procedia Engineering*, **2012**, 47, 1165-1172 10
- 142 Cognitive memory network. *Electronics Letters*, **2010**, 46, 677 1.1 10
- 141 Growth Mechanism of Cubic-Silicon Carbide Nanowires. *Journal of Nanomaterials*, **2009**, 2009, 1-5 3.2 10
- 140 Characterization of anodic SiO₂ films on P-type 4H-SiC. *Thin Solid Films*, **2009**, 517, 2808-2812 2.2 10
- 139 Aluminum induced in situ crystallization of amorphous SiC. *Applied Physics Letters*, **2009**, 94, 181909 3.4 10
- 138 Silicon carbide as a material for mainstream electronics. *Microelectronic Engineering*, **2006**, 83, 123-125 2.5 10
- 137 Investigation of electron-hole generation in MOS capacitors on 4H SiC. *IEEE Transactions on Electron Devices*, **2003**, 50, 1433-1439 2.9 10
- 136 Improved Operation of Micromechanical Comb-Drive Actuators through the Use of a New Angled Comb Finger Design. *Journal of Intelligent Material Systems and Structures*, **1998**, 9, 283-290 2.3 10

135	Ultra-thin dielectrics for semiconductor applications: growth and characteristics. <i>Microelectronics Journal</i> , 1991 , 22, 3-38	1.8	10
134	The Role of Near-Interface Traps in Modulating the Barrier Height of SiC Schottky Diodes. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 1675-1680	2.9	10
133	Influence of external mechanical stress on electrical properties of single-crystal n-3C-SiC/p-Si heterojunction diode. <i>Applied Physics Express</i> , 2015 , 8, 061302	2.4	9
132	Piezo-Hall effect in single crystal p-type 3C-SiC(100) thin film grown by low pressure chemical vapor deposition. <i>RSC Advances</i> , 2016 , 6, 31191-31195	3.7	9
131	Ranked selection of nearest discriminating features. <i>Human-centric Computing and Information Sciences</i> , 2012 , 2, 12	5.4	9
130	Measurement of plasma etch damage by a new slow trap profiling technique. <i>IEEE Electron Device Letters</i> , 1996 , 17, 515-517	4.4	9
129	Yield model for in-line integrated circuit production control. <i>Solid-State Electronics</i> , 1988 , 31, 975-979	1.7	9
128	A method for extraction of electron mobility in power HEMTs. <i>Superlattices and Microstructures</i> , 2015 , 85, 543-550	2.8	8
127	Effects of rapid thermal annealing on structural, chemical, and electrical characteristics of atomic-layer deposited lanthanum doped zirconium dioxide thin film on 4H-SiC substrate. <i>Applied Surface Science</i> , 2016 , 365, 296-305	6.7	8
126	Kinetic surface roughening and wafer bow control in heteroepitaxial growth of 3C-SiC on Si(111) substrates. <i>Scientific Reports</i> , 2015 , 5, 15423	4.9	8
125	The fabrication and characterization of 4H-SiC power UMOSFETs. <i>Chinese Physics B</i> , 2013 , 22, 027302	1.2	8
124	Effects of temperature and crucible height on the synthesis of 6H-SiC nanowires and nanoneedles. <i>Journal of Alloys and Compounds</i> , 2009 , 481, 345-348	5.7	8
123	Current mechanisms in n-SiC/p-Si heterojunctions. <i>Optoelectronic and Microelectronic Materials and Devices (COMMAD), Conference on</i> , 2008 ,		8
122	Turn-Around of Threshold Voltage in Gate Bias Stressed p-Channel Power Vertical Double-Diffused Metal-Oxide-Semiconductor Transistors. <i>Japanese Journal of Applied Physics</i> , 2008 , 47, 6272-6276	1.4	8
121	Electrical Properties of Atomic-Layer-Deposited La ₂ O ₃ /Thermal-Nitrided SiO ₂ Stacking Dielectric on 4H-SiC(0001). <i>Materials Science Forum</i> , 2007 , 556-557, 643-646	0.4	8
120	Electronic Properties of SiON/HfO ₂ Insulating Stacks on 4H-SiC (0001). <i>Materials Science Forum</i> , 2004 , 457-460, 1361-1364	0.4	8
119	Self-alignment of optical fibers with optical quality end-polished silicon rib waveguides using wet chemical micromachining techniques. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 1999 , 5, 1249-1254	3.8	8
118	UV-Radiation Annealing of the Electron- and X-Irradiation Damaged CMOS Transistors. <i>Physica Status Solidi A</i> , 1992 , 129, 569-575		8

117	Temperature and doping dependence of the Raman scattering in 4H-SiC. <i>Optical Materials Express</i> , 2016 , 6, 2725	2.6	8
116	A large pseudo-Hall effect in n-type 3C-SiC(1 0 0) and its dependence on crystallographic orientation for stress sensing applications. <i>Materials Letters</i> , 2018 , 213, 11-14	3.3	8
115	Mechanism of leakage current increase in p-GaN gate AlGaN/GaN power devices induced by ON-state gate bias. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 124101	1.4	8
114	Thermoresistance of p-Type 4H-SiC Integrated MEMS Devices for High-Temperature Sensing. <i>Advanced Engineering Materials</i> , 2019 , 21, 1801049	3.5	7
113	Effect of Oxidation Time on Thermally Grown Oxide on GaN. <i>Journal of Materials Engineering and Performance</i> , 2013 , 22, 1341-1347	1.6	7
112	Experimental Evaluation of Different Passivation Layers on the Performance of 3kV 4H-SiC BJTs. <i>Materials Science Forum</i> , 2010 , 645-648, 661-664	0.4	7
111	Synthesis and characterization of silica/titania nanocomposite via a combination of sol-gel and mechanochemical process. <i>Journal of Alloys and Compounds</i> , 2008 , 466, 304-307	5.7	7
110	Effects of precursor aging and post-deposition treatment time on photo-assisted sol-gel derived low-dielectric constant SiO ₂ thin film on Si. <i>Microelectronics Journal</i> , 2007 , 38, 227-230	1.8	7
109	Return-map-based approaches for noncoherent detection in chaotic digital communications. <i>IEEE Transactions on Circuits and Systems Part 1: Regular Papers</i> , 2002 , 49, 1495-1499		7
108	Dielectrics on Silicon Thermally Grown or Annealed in a Nitrogen Rich Environment. <i>Materials Research Society Symposia Proceedings</i> , 1994 , 342, 151		7
107	Analysis of temperature dependence of CMOS transistors' threshold voltage. <i>Microelectronics Reliability</i> , 1991 , 31, 33-37	1.2	7
106	Mechanisms of positive gate-bias stress induced instabilities in CMOS transistors. <i>Microelectronics Reliability</i> , 1987 , 27, 1001-1016	1.2	7
105	Power-switching applications beyond silicon: The status and future prospects of SiC and GaN devices 2014 ,		6
104	Color Chart for Thin SiC Films Grown on Si Substrates. <i>Materials Science Forum</i> , 2013 , 740-742, 279-282	0.4	6
103	Effects of rapid thermal annealing on Al ₂ O ₃ /SiN reaction barrier layer/thermal-nitrided SiO ₂ stacking gate dielectrics on n-type 4H-SiC. <i>Applied Physics Letters</i> , 2010 , 96, 122108	3.4	6
102	Slow current transients in metal-oxide-semiconductor capacitors. <i>Applied Physics Letters</i> , 1995 , 66, 2510-2512	3.4	6
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